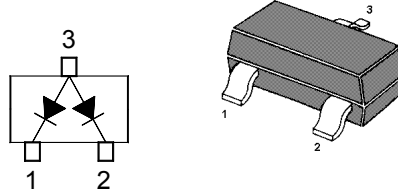


## Silicon Epitaxial Planar Schottky Barrier Diode



Marking Code: "XY"  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

| Parameter                     | Symbol    | Value         | Unit             |
|-------------------------------|-----------|---------------|------------------|
| Reverse Voltage               | $V_R$     | 30            | V                |
| Forward Current (Single)      | $I_F$     | 30            | mA               |
| Forward Current (Double)      |           | 20            |                  |
| Peak Forward Current (Single) | $I_{FM}$  | 150           | mA               |
| Peak Forward Current (Double) |           | 110           |                  |
| Junction Temperature          | $T_j$     | 125           | $^\circ\text{C}$ |
| Storage Temperature Range     | $T_{stg}$ | - 55 to + 125 | $^\circ\text{C}$ |

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter   | Symbol   | Typ. | Max. | Unit          |
|---|----------|------|------|---------------|
| Forward Voltage<br>at $I_F = 1\text{ mA}$<br>at $I_F = 30\text{ mA}$                                  | $V_F$    | -    | 0.4  | V             |
|   |          | -    | 1    |               |
| Reverse Current<br>at $V_R = 30\text{ V}$   | $I_R$    | -    | 1    | $\mu\text{A}$ |
| Terminal Capacitance<br>at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$                                    | $C_t$    | 2.7  | -    | pF            |
| Reverse Recovery Time<br>at $I_F = I_R = 10\text{ mA}$ , $I_{tr} = 1\text{ mA}$ , $R_L = 100\ \Omega$ | $t_{rr}$ | 1    | -    | ns            |



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